

ABSTRACT

A fabrication system utilizes a protocol for removing native oxide from a top surface of a wafer. An exposure to a plasma, such as a plasma containing hydrogen and argon can remove the native oxide from
5 the top surface without causing excessive germanium contamination. The protocol can use a hydrogen fluoride dip. The hydrogen fluoride dip can be used before the plasma is used. The protocol allows better silicidation in SMOS devices.